

Description

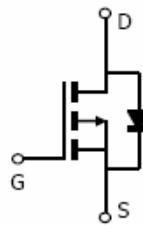
The G13P04S uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

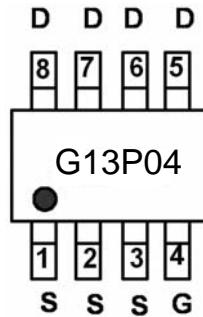
- V_{DSS} $R_{DS(ON)}$ @10V (Typ) I_D
- -40V 12 mΩ -13A
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation
- RoHS Compliant

Application

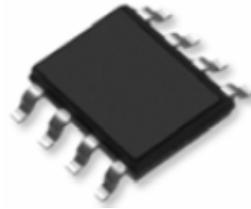
- Power switching application
- Hard switched and high frequency circuits
- DC-DC converter



Schematic diagram



Marking and pin assignment



SOP-8 top view

Ordering Information

Part Number	Marking	Case	Packaging
G13P04S	G13P04	SOP-8	4000pcs/Reel

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-13	A
Drain Current-Continuous($T_C=100^\circ\text{C}$)	I_D (100°C)	-9	A
Pulsed Drain Current	I_{DM}	50	A
Maximum Power Dissipation	P_D	2.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

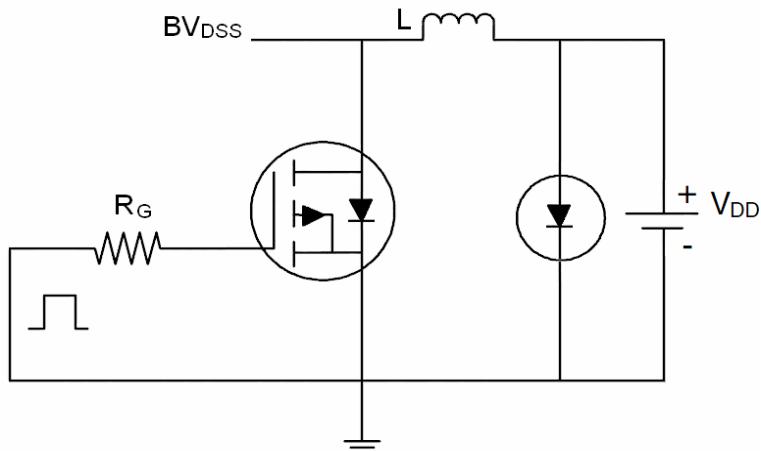
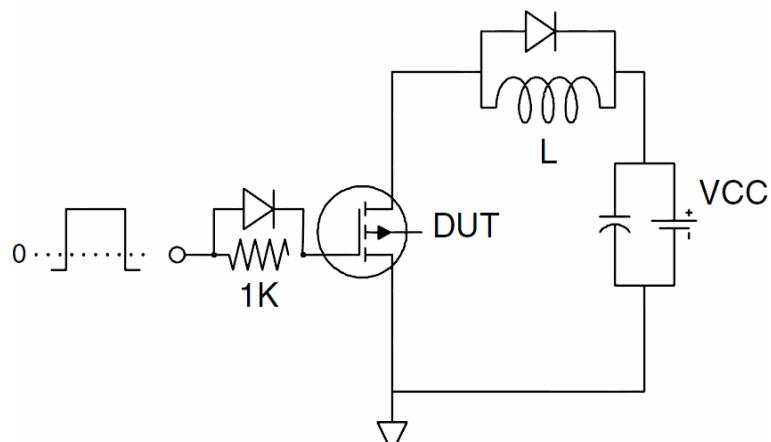
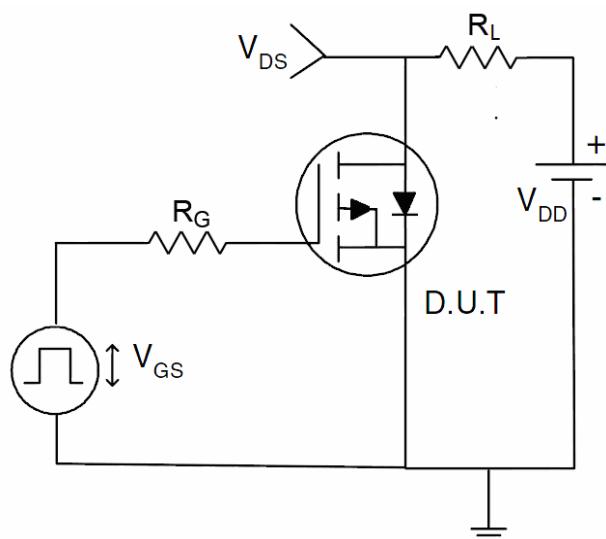
Thermal Resistance ,Junction-to-Ambient(Note 2)	$R_{\theta JA}$	50	°C/W
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-40\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1.3	-2	-2.5	V
Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-12\text{A}$	-	12	15	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-10\text{A}$	35	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{\text{DS}}=-20\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	2800	-	PF
Output Capacitance	C_{oss}		-	320	-	PF
Reverse Transfer Capacitance	C_{rss}		-	220	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=-20\text{V}, R_{\text{L}}=2\Omega, V_{\text{GS}}=-10\text{V}, R_{\text{GEN}}=6\Omega$	-	11	-	nS
Turn-on Rise Time	t_{r}		-	75	-	nS
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	89	-	nS
Turn-Off Fall Time	t_{f}		-	35	-	nS
Total Gate Charge	Q_{g}	$V_{\text{DS}}=-20\text{V}, I_{\text{D}}=-12\text{A}, V_{\text{GS}}=-10\text{V}$	-	40	-	nC
Gate-Source Charge	Q_{gs}		-	6	-	nC
Gate-Drain Charge	Q_{gd}		-	12	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=-12\text{A}$	-	-	1.2	V
Diode Forward Current (Note 2)	I_{S}		-	-	-13	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test Circuit**1) E_{AS} Test Circuit****2) Gate Charge Test Circuit****3) Switch Time Test Circuit**

Typical Electrical and Thermal Characteristics (Curves)

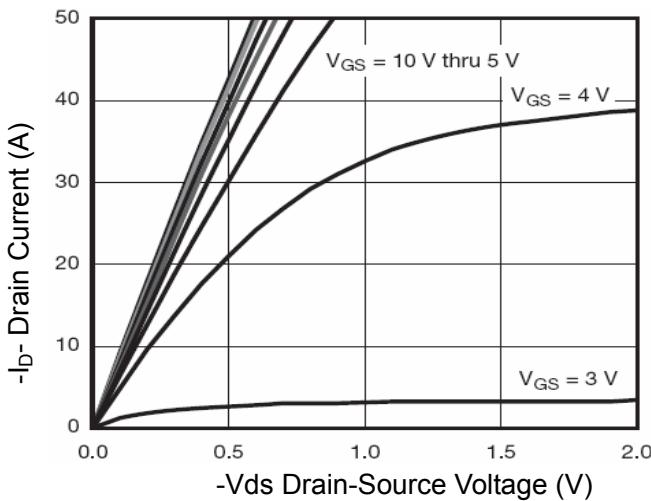


Figure 1 Output Characteristics

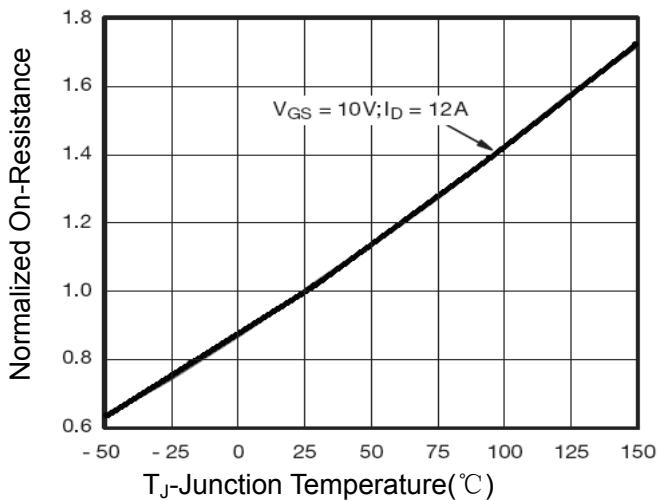


Figure 4 Rdson-Junction Temperature

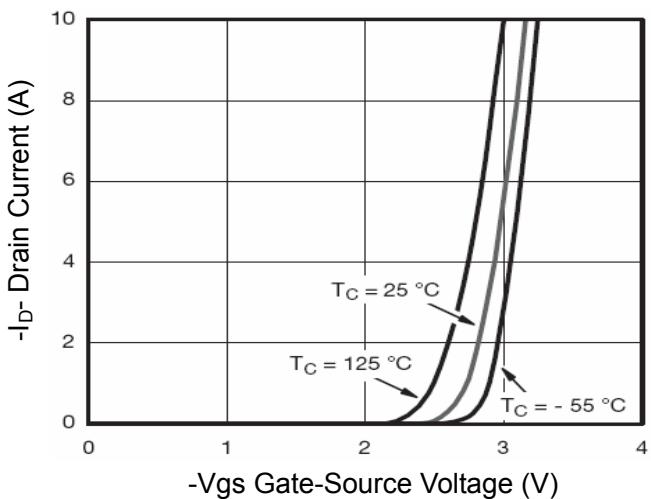


Figure 2 Transfer Characteristics

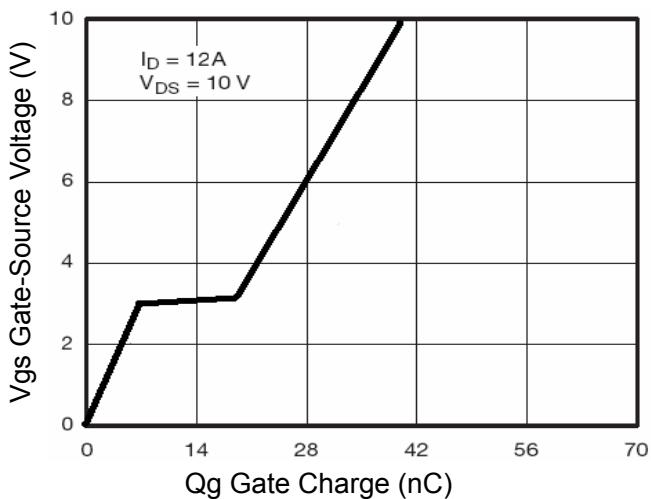


Figure 5 Gate Charge

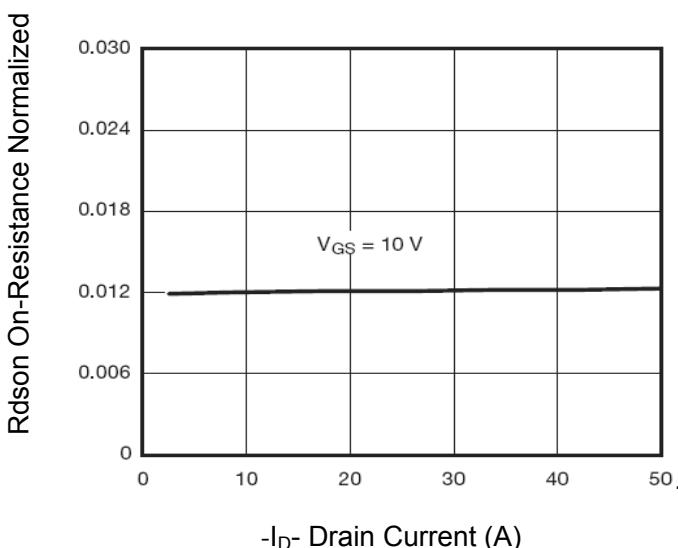


Figure 3 Rdson- Drain Current

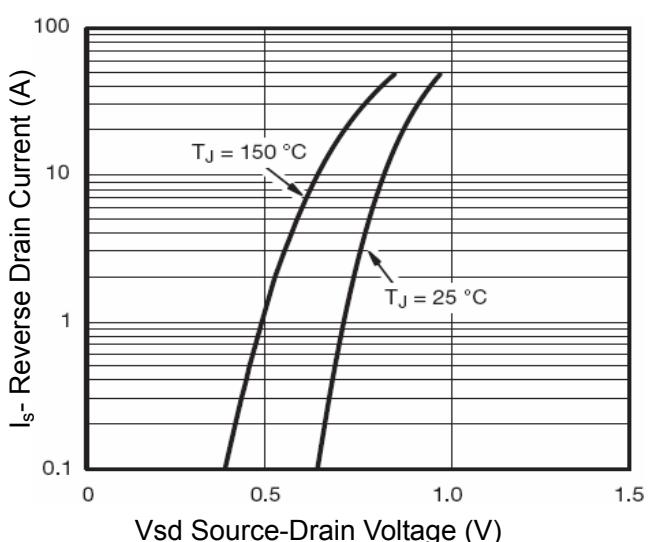


Figure 6 Source- Drain Diode Forward

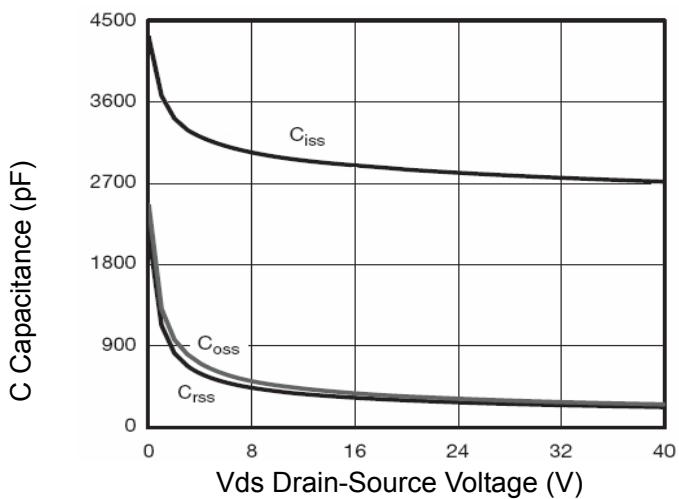


Figure 7 Capacitance vs Vds

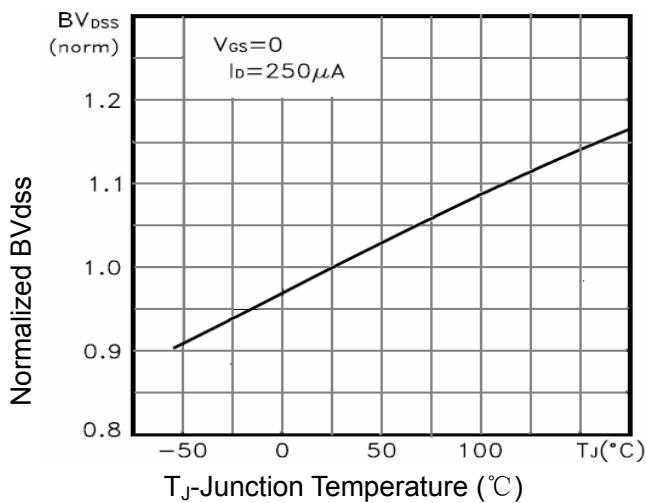


Figure 9 BV_{dss} vs Junction Temperature

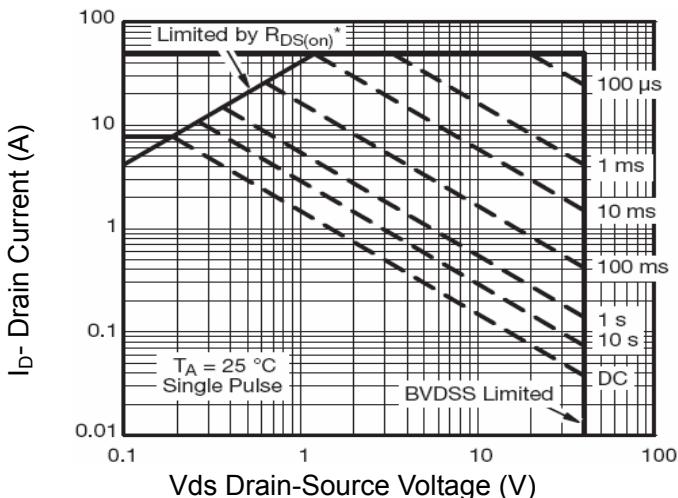


Figure 8 Safe Operation Area

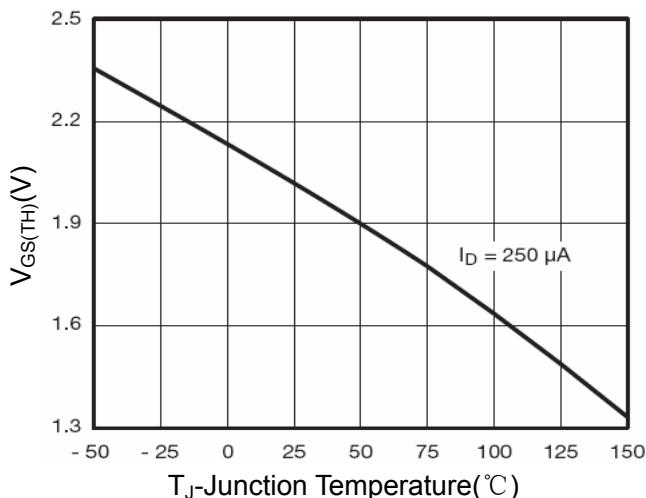


Figure 10 $V_{GS(th)}$ vs Junction Temperature

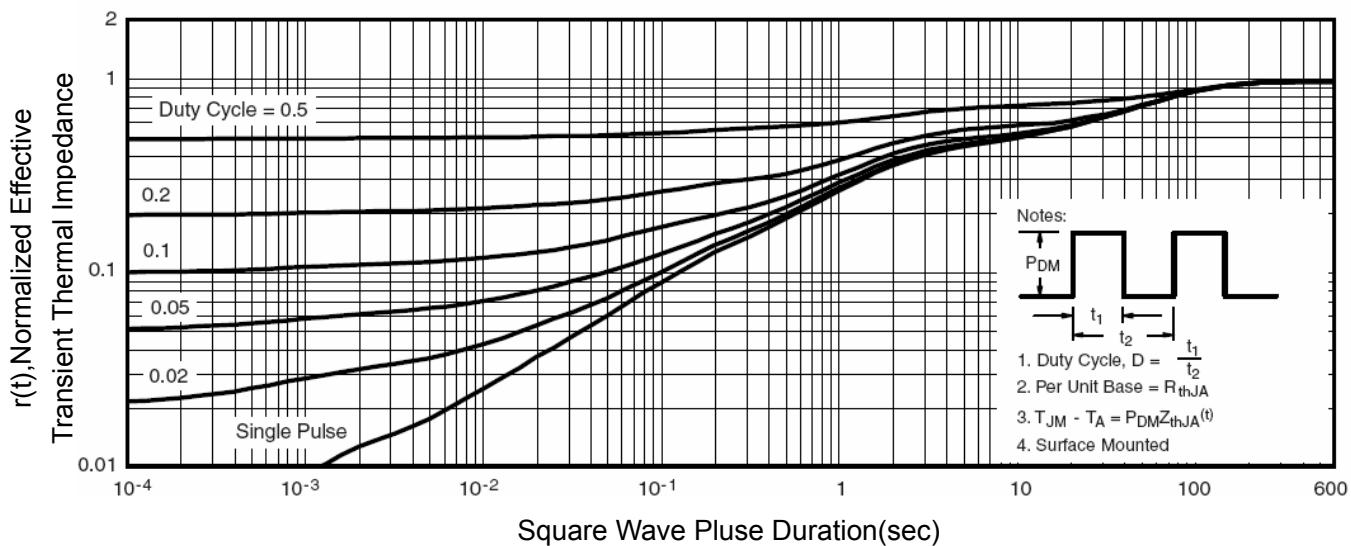
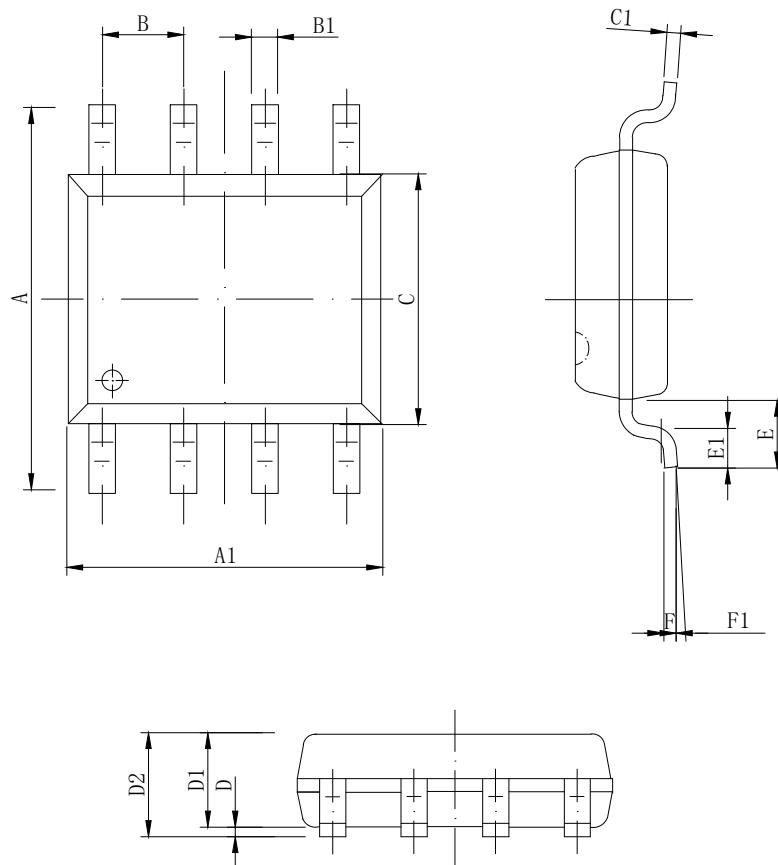


Figure 11 Normalized Maximum Transient Thermal Impedance

SOP-8 Package information



DIM	MIN	NOM	MAX
A	5.800	6.000	6.200
A1	4.800	4.900	5.000
B	1.270BSC		
B1	0.35 ^ 8x	0.40 ^ 8x	0.45 ^ 8x
C	3.780	3.880	3.980
C1	-	0.203	0.253
D	0.050	0.150	0.250
D1	1.350	1.450	1.550
D2	1.500	1.600	1.700
E	1.060 REF		
E1	0.400	0.700	0.100
F	0.250BSC		
F1	2°	4°	6°

All Dimensions in mm